

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









### 8 A Snubberless™ Triac

#### Datasheet - production data

#### **Features**

- High static and dynamic commutation
- Package is RoHS (2002/95/EC) compliant
- High surge current
- ECOPACK<sup>®</sup>2 compliant component
- Complies with UL standards (File ref: E81734)

### **Applications**

- General purpose AC switching
- Motor control circuits in power tools
- Home appliances
- Lighting

### **Description**

The T830-8FP Triac can be used for the on/off function in general purpose AC switching where high commutation capability is required.

Provides insulation rated at 1500 V rms.

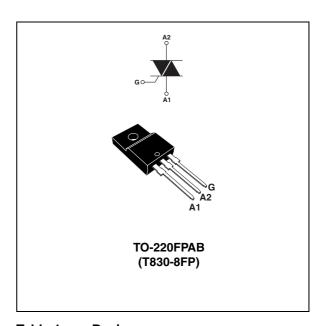


Table 1. Device summary

| <u> </u>            |       |      |  |
|---------------------|-------|------|--|
| Symbol              | Value | Unit |  |
| I <sub>T(rms)</sub> | 8     | Α    |  |
| $V_{DRM}, V_{RRM}$  | 800   | V    |  |
| $V_{DSM}, V_{RSM}$  | 900   | V    |  |
| I <sub>GT</sub>     | 30    | mA   |  |

Characteristics T830-8FP

## 1 Characteristics

Table 2. Absolute ratings (limiting values)

| Symbol                                 | Parameter  |                        |                         | Value                          | Unit             |
|--|--|------------------------|-------------------------|--------------------------------|------------------|
| I <sub>T(rms)</sub>                    | On-state rms current (full sine wave)  |                        | T <sub>c</sub> = 95 °C  | 8                              | Α                |
| l                                      | Non repetitive surge peak on-state   | F = 50 Hz              | t = 20 ms               | 80                             | Α                |
| I <sub>TSM</sub>                       | current (full cycle, $T_j$ initial = 25 °C)  | F = 60 Hz              | t = 16.7 ms             | 84                             | ^                |
| l <sup>2</sup> t                       | I <sup>2</sup> t Value for fusing  | t <sub>p</sub> = 10 ms | t <sub>p</sub> = 10 ms  |                                | A <sup>2</sup> s |
| dI/dt                                  | Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $t_r \le 100 \text{ ns}$ | F = 120 Hz             | T <sub>j</sub> = 125 °C | 100                            | A/μs             |
| V <sub>DSM</sub> ,<br>V <sub>RSM</sub> | Non repetitive surge peak on-state voltage   | t <sub>p</sub> = 10 ms | T <sub>j</sub> = 25 °C  | 900                            | ٧                |
| I <sub>GM</sub>                        | Peak gate current  | t <sub>p</sub> = 20 μs | T <sub>j</sub> = 125 °C | 4                              | Α                |
| P <sub>G(AV)</sub>                     | Average gate power dissipation $T_j = 125 ^{\circ}\text{C}$                                  |                        |                         | 1                              | W                |
| T <sub>stg</sub>                       | Storage junction temperature range Operating junction temperature range                      |                        |                         | - 40 to + 150<br>- 40 to + 125 | °C               |
| TL                                     | Lead temperature for soldering during 10 s (at 4 mm from case)                               |                        |                         | 260                            | °C               |
| V <sub>ins</sub>                       | Insulation rms voltage, 1 minute   |                        |                         | 1500                           | V                |

Table 3. Electrical characteristics ( $T_j = 25$  °C, unless otherwise specified)

| Symbol                         | Test conditions Quadrant  |                         |        | Value | Unit |
|--------------------------------|---|-------------------------|--------|-------|------|
| I <sub>GT</sub> <sup>(1)</sup> | $V_D = 12 \text{ V, R}_L = 30 \Omega$   | I - II - III Max.       | May    | 30    | mA   |
| $V_{GT}$                       | VD = 12 V, 11[ = 30 \$2   |                         | iviax. | 1.3   | V    |
| $V_{GD}$                       | $V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, T_j = 125 \text{ °C}$ I - II - III |                         | Min.   | 0.2   | V    |
| I <sub>H</sub> <sup>(2)</sup>  | I <sub>T</sub> = 250 mA   |                         | Max.   | 50    | mA   |
| ΙL                             | $I_{G} = 1.2 I_{GT}$ $I - II - III$   |                         | Max.   | 60    | mA   |
| dV/dt                          | $V_D = 67\%V_{DRM}$ , gate open $T_j = 125$                                   |                         | Min.   | 2500  | V/µs |
| (dl/dt)c                       | Without snubber   | T <sub>j</sub> = 125 °C | Min.   | 10.0  | A/ms |

<sup>1.</sup> Minimum  $I_{GT}$  is guaranteed at 5% of  $I_{GT}$  max.

<sup>2.</sup> For both polarities of A2 referenced to A1.

T830-8FP Characteristics

Table 4. Static characteristics

| Symbol                        | Test conditions                                   |                         |        | Value | Unit |
|-------------------------------|---|-------------------------|--------|-------|------|
| V <sub>T</sub> <sup>(1)</sup> | $I_{TM} = 11 \text{ A}, t_p = 380 \ \mu \text{s}$ | T <sub>j</sub> = 25 °C  | Max.   | 1.55  | V    |
| V <sub>t0</sub> (1)           | Threshold voltage                                 | T <sub>j</sub> = 125 °C | Max.   | 0.85  | V    |
| R <sub>d</sub> <sup>(1)</sup> | Dynamic resistance                                | T <sub>j</sub> = 125 °C | Max.   | 40    | mΩ   |
| I <sub>DRM</sub>              | V -V  | T <sub>j</sub> = 25 °C  | Max.   | 5     | μΑ   |
| I <sub>RRM</sub>              | $V_{DRM} = V_{RRM}$                               | T <sub>j</sub> = 125 °C | iviax. | 1     | mA   |

<sup>1.</sup> For both polarities of A2 referenced to A1.

Table 5. Thermal resistance

| Symbol               | Parameter             | Value | Unit |
|----------------------|-----------------------|-------|------|
| R <sub>th(j-c)</sub> | Junction to case (AC) | 3.5   | °C/W |
| R <sub>th(j-a)</sub> | Junction to ambient   | 60    | °C/W |

Figure 1. Maximum power dissipation versus Figure 2. On-state rms current versus case rms on-state current temperature

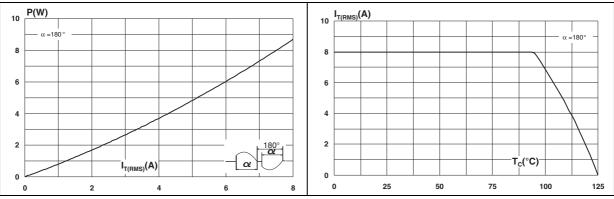
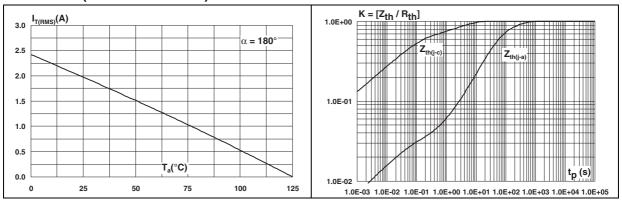


Figure 3. On-state rms current versus ambient temperature (free air convection)

Figure 4. Relative variation of thermal impedance versus pulse duration



Characteristics T830-8FP

Figure 5. Relative variation of gate trigger current versus junction temperature (typical values)

Figure 6. Relative variation of gate trigger voltage versus junction temperature (typical values)

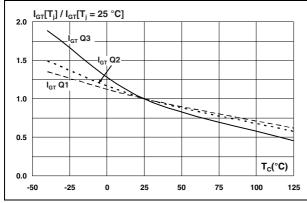
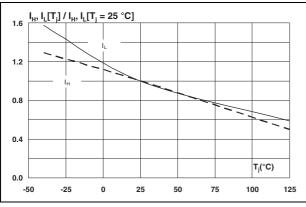


Figure 7. Relative variation of holding and latching current versus junction temperature (typical values)

Figure 8. Surge peak on-state current versus number of cycles



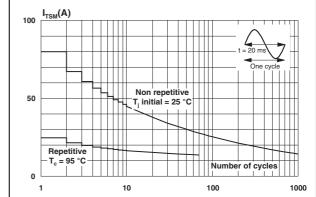
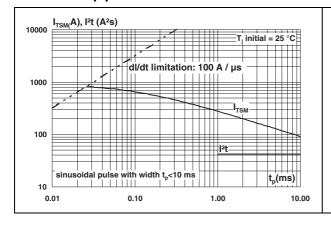
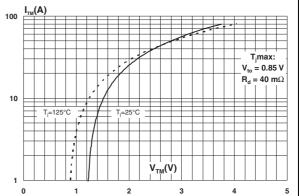


Figure 9. Non repetitive surge peak on-state Figure 10. current and corresponding value of I<sup>2</sup>T

igure 10. On-state characteristics (maximum values)





T830-8FP Characteristics

Figure 11. Relative variation of critical rate of Figure 12. Relative variation of static dV/dt decrease of main current versus immunity versus junction junction temperature temperature (typical values)

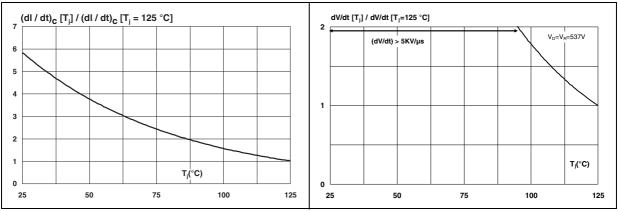
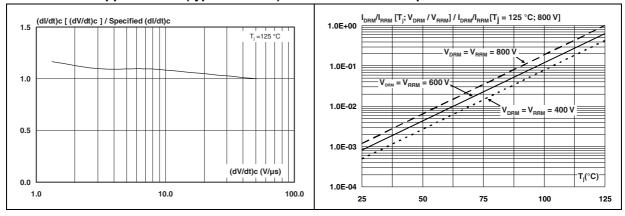


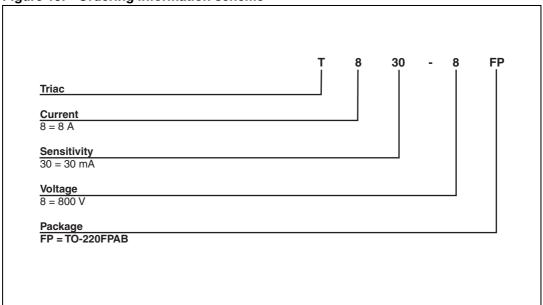
Figure 13. Relative variation of critical rate of Figure 14. decrease of main current versus reapplied dV/dt (typical values)

Figure 14. Relative variation of leakage current versus junction temperature



# 2 Ordering information scheme

Figure 15. Ordering information scheme



T830-8FP Package information

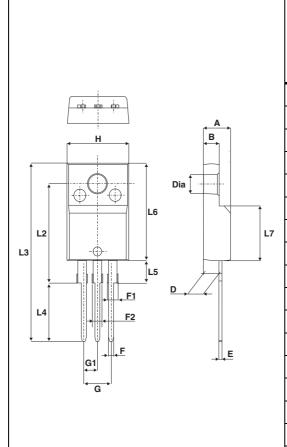
## 3 Package information

Epoxy meets UL94, V0

Recommended torque: 0.4 to 0.6 N⋅m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK $^{\circledR}$  packages, depending on their level of environmental compliance. ECOPACK $^{\circledR}$  specifications, grade definitions and product status are available at: www.st.com. ECOPACK $^{\circledR}$  is an ST trademark.

Table 6. TO-220FPAB Dimensions



|      | Dimensions  |      |           |       |
|------|-------------|------|-----------|-------|
| Ref. | Millimeters |      | Inc       | hes   |
|      | Min.        | Max. | Min.      | Max.  |
| Α    | 4.4         | 4.6  | 0.173     | 0.181 |
| В    | 2.5         | 2.7  | 0.098     | 0.106 |
| D    | 2.5         | 2.75 | 0.098     | 0.108 |
| Е    | 0.45        | 0.70 | 0.018     | 0.027 |
| F    | 0.75        | 1    | 0.030     | 0.039 |
| F1   | 1.15        | 1.70 | 0.045     | 0.067 |
| F2   | 1.15        | 1.70 | 0.045     | 0.067 |
| G    | 4.95        | 5.20 | 0.195     | 0.205 |
| G1   | 2.4         | 2.7  | 0.094     | 0.106 |
| Η    | 10          | 10.4 | 0.393     | 0.409 |
| L2   | 16 Typ.     |      | 0.63 Typ. |       |
| L3   | 28.6        | 30.6 | 1.126     | 1.205 |
| L4   | 9.8         | 10.6 | 0.386     | 0.417 |
| L5   | 2.9         | 3.6  | 0.114     | 0.142 |
| L6   | 15.9        | 16.4 | 0.626     | 0.646 |
| L7   | 9.00        | 9.30 | 0.354     | 0.366 |
| Dia. | 3.00        | 3.20 | 0.118     | 0.126 |

Ordering information T830-8FP

# 4 Ordering information

 Table 7.
 Ordering information

| Order code | Marking  | Package    | Weight | Base qty | Delivery mode |
|------------|----------|------------|--------|----------|---------------|
| T830-8FP   | T830-8FP | TO-220FPAB | 2.0 g  | 50       | Tube          |

# 5 Revision history

Table 8. Document revision history

| Date        | Revision | Changes          |
|-------------|----------|------------------|
| 24-Sep-2012 | 1        | Initial release. |

#### Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2012 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

